

## POWER SCHOTTKY RECTIFIER

### MAIN PRODUCT CHARACTERISTICS

|            |         |
|------------|---------|
| $I_F(AV)$  | 2 x 3 A |
| $V_{RRM}$  | 40 V    |
| $T_j(max)$ | 150 °C  |
| $V_F(max)$ | 0.57 V  |

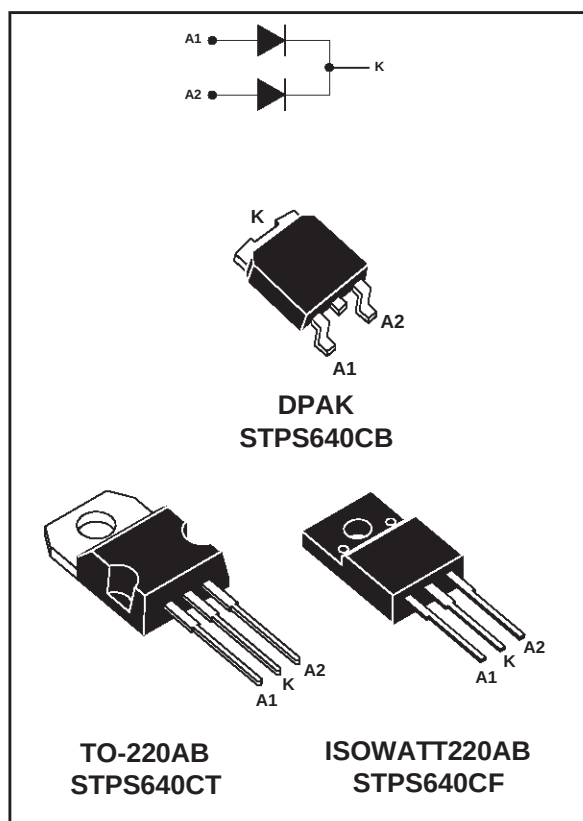
### FEATURES AND BENEFITS

- VERY SMALL CONDUCTION LOSSES
- NEGLIGIBLE SWITCHING LOSSES
- EXTREMELY FAST SWITCHING
- LOW FORWARD DROP VOLTAGE
- LOW CAPACITANCE
- LOW THERMAL RESISTANCE
- INSULATED PACKAGE:  
Insulating voltage = 2000V DC  
Capacitance = 12pF
- SMD PACKAGE (tape and reel option: -TR)

### DESCRIPTION

Dual Schottky rectifier suited to Switch Mode Power Supplies and other Power Converters.

This device is intended for use in low and medium voltage operation, and particularly, in high frequency circuitries where low switching losses are required (free wheeling and polarity protection).



### ABSOLUTE RATINGS (limiting values, per diode)

| Symbol              | Parameter                                |                           |                        | Value         | Unit |
|---------------------|------------------------------------------|---------------------------|------------------------|---------------|------|
| V <sub>RRM</sub>    | Repetitive peak reverse voltage          |                           |                        | 40            | V    |
| I <sub>F(RMS)</sub> | RMS forward current                      | TO-220AB / ISOWATT220AB   |                        | 10            | A    |
|                     |                                          | DPAK                      |                        | 6             |      |
| I <sub>F(AV)</sub>  | Average forward current δ = 0.5          | TO-220AB                  | T <sub>c</sub> = 135°C | 3             | A    |
|                     |                                          | ISOWATT220AB              | T <sub>c</sub> = 130°C |               |      |
|                     |                                          | DPAK                      | T <sub>c</sub> = 120°C |               |      |
| I <sub>FSM</sub>    | Surge non repetitive forward current     | tp = 10 ms Sinusoidal     |                        | 75            | A    |
| I <sub>RRM</sub>    | Repetitive peak reverse current          | tp = 2 μs F = 1kHz square |                        | 1             | A    |
| T <sub>stg</sub>    | Storage temperature range                |                           |                        | - 65 to + 150 | °C   |
| T <sub>j</sub>      | Maximum operating junction temperature   |                           |                        | 150           | °C   |
| dV/dt               | Critical rate of rise of reverse voltage |                           |                        | 10000         | V/μs |

**THERMAL RESISTANCES**

| Symbol        | Parameter        |               |                    | Value      | Unit                 |
|---------------|------------------|---------------|--------------------|------------|----------------------|
| $R_{th(j-c)}$ | Junction to case | TO-220AB/DPAK | Per diode<br>Total | 5.5<br>3   | $^{\circ}\text{C/W}$ |
|               |                  | ISOWATT220AB  | Per diode<br>Total | 7.5<br>5.2 |                      |
| $R_{th(c)}$   | Coupling         | TO-220AB      |                    | 0.5        | $^{\circ}\text{C/W}$ |
|               |                  | ISOWATT220AB  |                    | 3          |                      |

When the diodes 1 and 2 are used simultaneously:

$$\Delta T_j(\text{diode 1}) = P(\text{diode 1}) \times R_{th(j-c)}(\text{Per diode}) + P(\text{diode 2}) \times R_{th(c)}$$

**STATIC ELECTRICAL CHARACTERISTICS (per diode)**

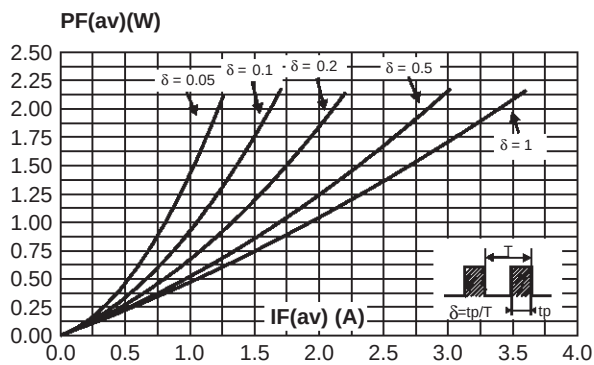
| Symbol  | Tests Conditions        |                             |                    | Min. | Typ. | Max. | Unit          |
|---------|-------------------------|-----------------------------|--------------------|------|------|------|---------------|
| $I_R^*$ | Reverse leakage current | $T_j = 25^{\circ}\text{C}$  | $V_R = V_{RRM}$    |      |      | 100  | $\mu\text{A}$ |
|         |                         | $T_j = 125^{\circ}\text{C}$ |                    |      | 2    | 10   | mA            |
| $V_F^*$ | Forward voltage drop    | $T_j = 25^{\circ}\text{C}$  | $I_F = 3\text{ A}$ |      |      | 0.63 | V             |
|         |                         | $T_j = 25^{\circ}\text{C}$  | $I_F = 6\text{ A}$ |      |      | 0.84 |               |
|         |                         | $T_j = 125^{\circ}\text{C}$ | $I_F = 3\text{ A}$ |      | 0.5  | 0.57 |               |
|         |                         | $T_j = 125^{\circ}\text{C}$ | $I_F = 6\text{ A}$ |      | 0.67 | 0.72 |               |
|         |                         |                             |                    |      |      |      |               |

Pulse test : \*  $t_p = 380\text{ }\mu\text{s}$ ,  $\delta < 2\%$

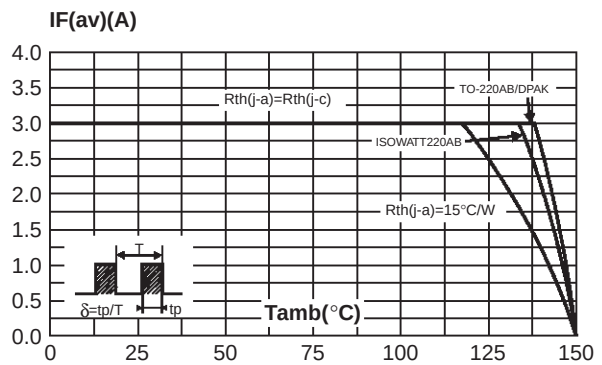
To evaluate the maximum conduction losses use the following equation :

$$P = 0.42 \times I_{F(AV)} + 0.050 I_F^2 (RMS)$$

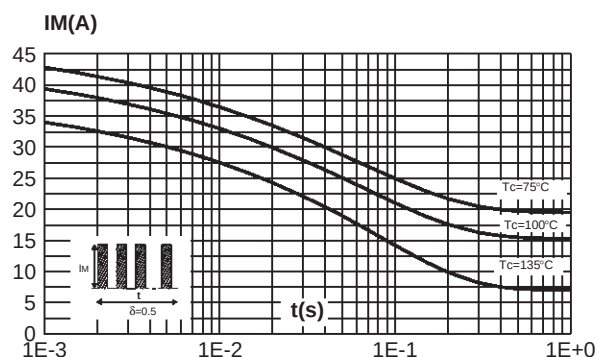
**Fig. 1:** Average forward power dissipation versus average forward current (per diode).



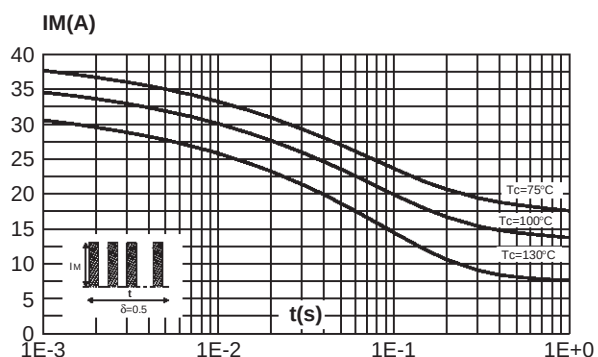
**Fig. 2:** Average current versus ambient temperature ( $\delta = 0.5$ , per diode).



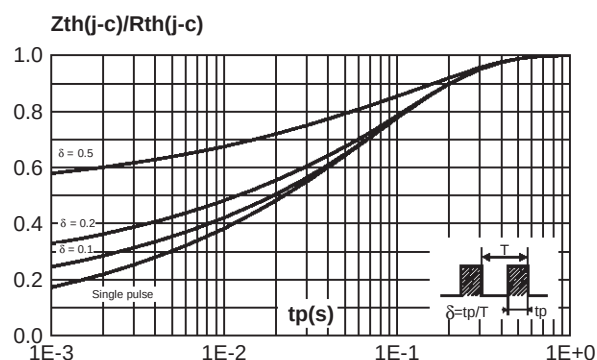
**Fig. 3-1:** Non repetitive surge peak forward current versus overload duration. (Maximum values, per diode) (TO-220AB/ DPAK).



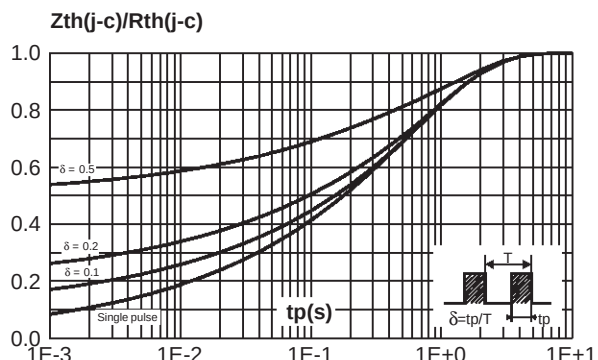
**Fig. 3-2:** Non repetitive surge peak forward current versus overload duration. (Maximum values, per diode) (ISOWATT220AB).



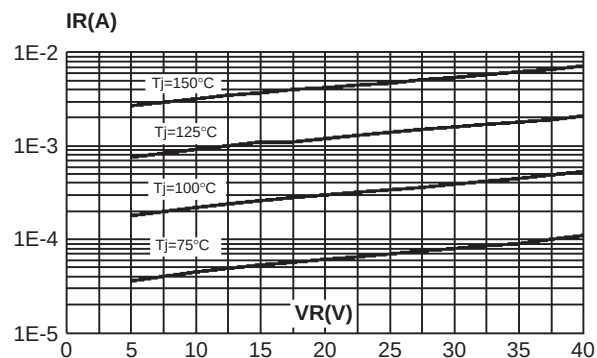
**Fig. 4.1:** Relative variation of thermal transient impedance junction to case versus pulse duration (TO-220AB / DPAK).



**Fig. 4-2:** Relative variation of thermal transient impedance junction to case versus pulse duration (ISOWATT220AB).



**Fig. 5:** Reverse leakage current versus reverse voltage applied (typical values, per diode).



**Fig. 6:** Junction capacitance versus reverse voltage applied (typical values, per diode).

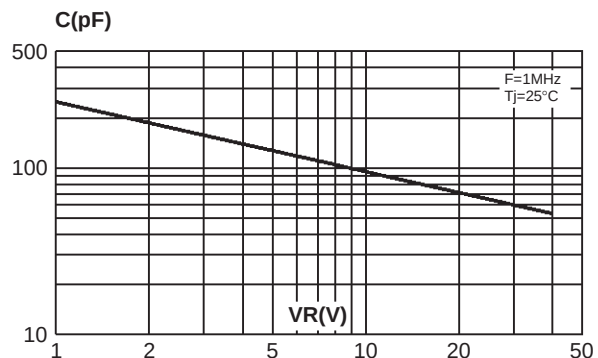


Fig. 7: Forward voltage drop versus forward current (maximum values, per diode).

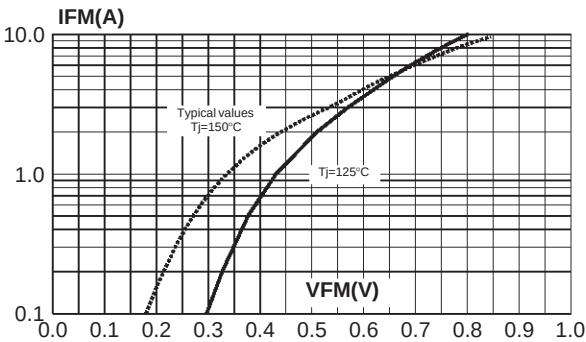
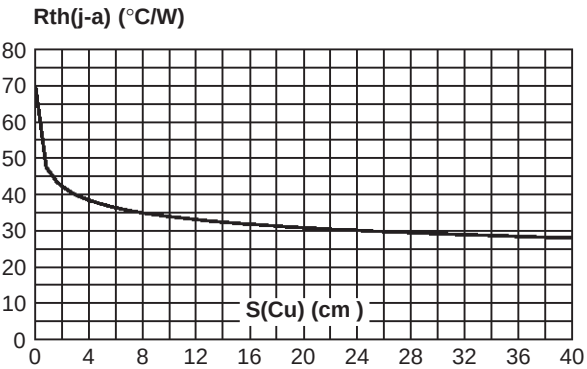
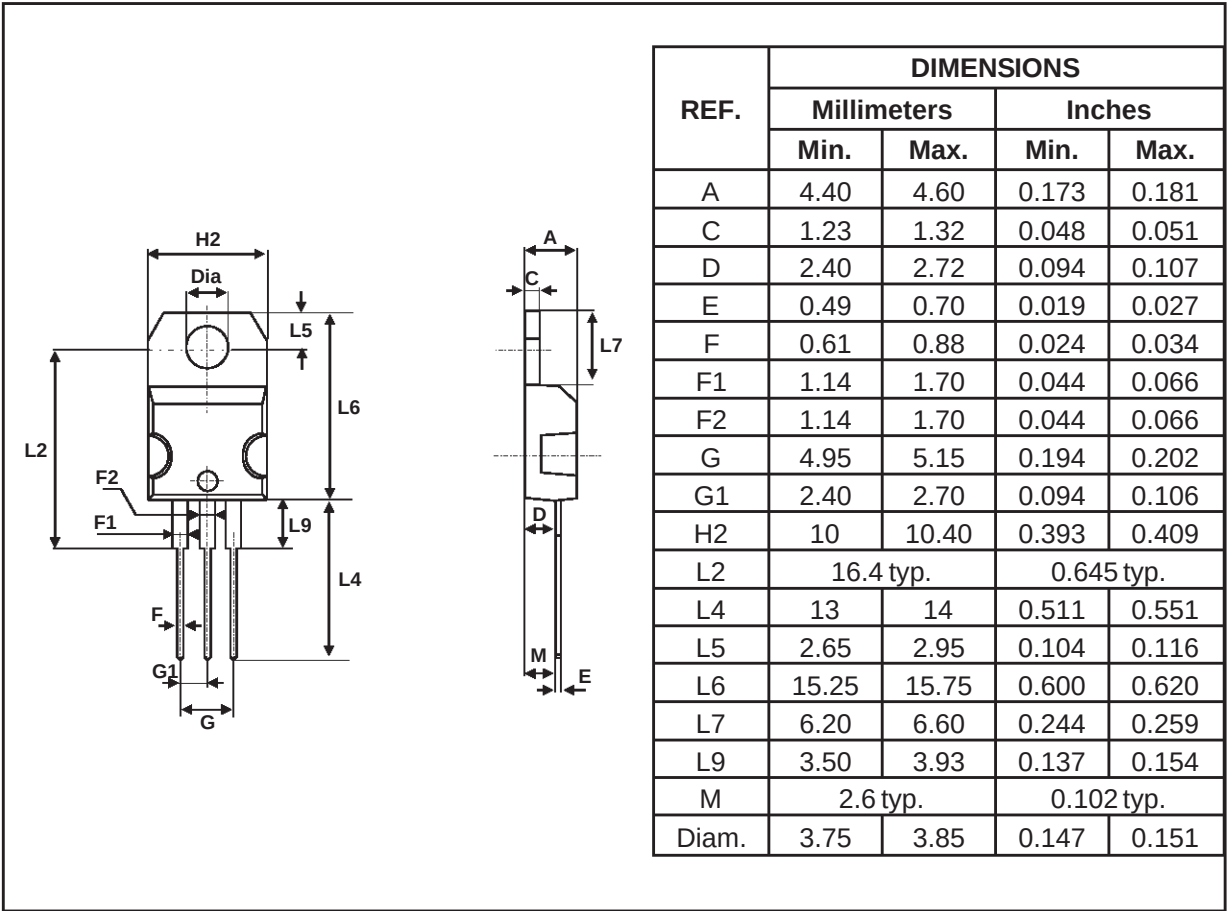


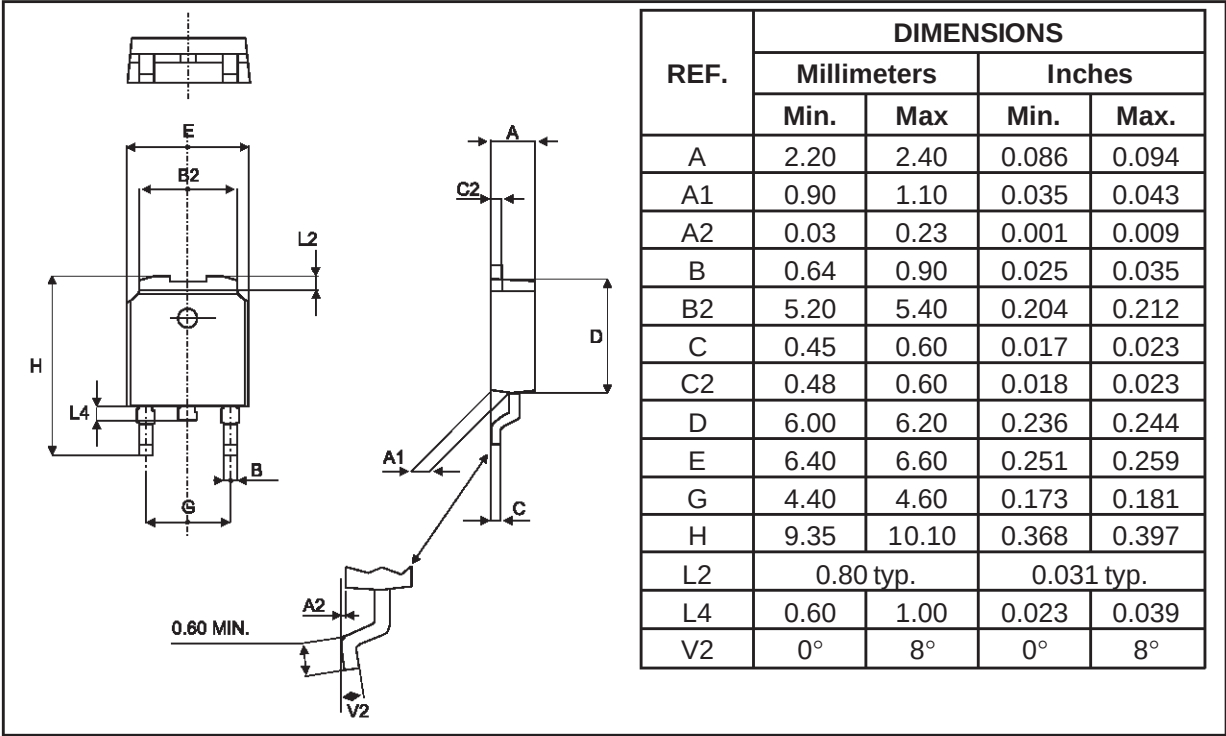
Fig. 8: Thermal resistance junction to ambient versus copper surface under tab (Epoxy printed circuit board FR4, copper thickness: 35μm).



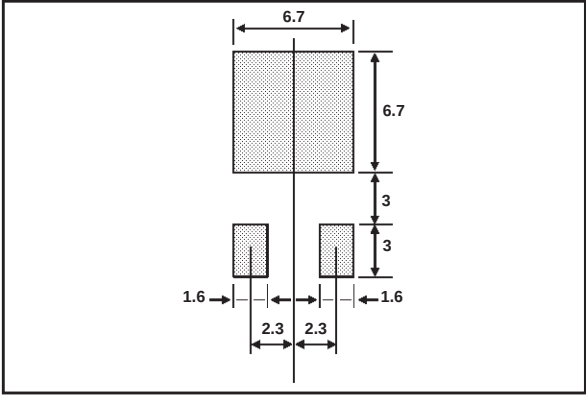
PACKAGE MECHANICAL DATA  
TO-220AB



PACKAGE MECHANICAL DATA  
DPAK

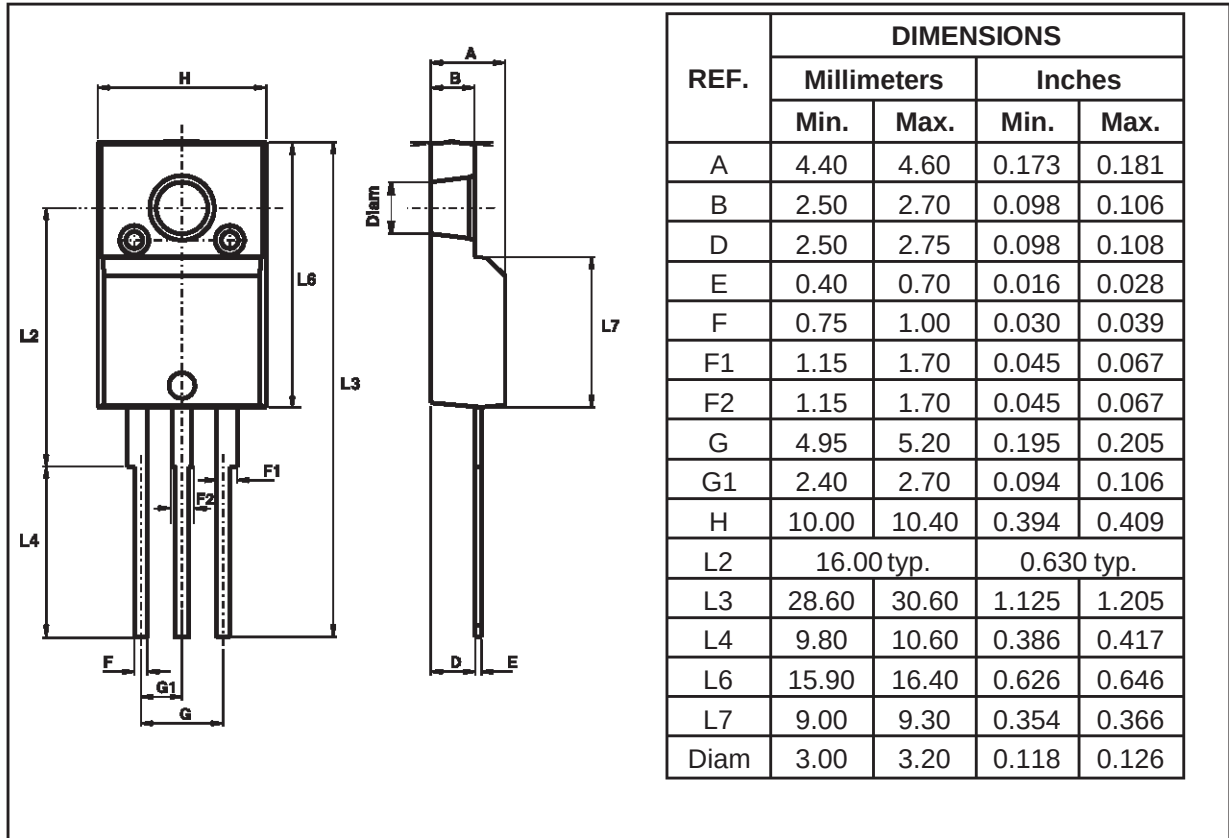


FOOTPRINT DIMENSIONS (in millimeters)



## STPS640CT/CF/CB

### PACKAGE MECHANICAL DATA ISOWATT220AB



| Ordering type | Marking   | Package      | Weight | Base qty | Delivery mode |
|---------------|-----------|--------------|--------|----------|---------------|
| STPS640CT     | STPS640CT | TO-220AB     | 2.20g  | 50       | Tube          |
| STPS640CB     | S640C     | DPAK         | 0.30g  | 75       | Tube          |
| STPS640CB-TR  | S640C     | DPAK         | 0.30g  | 2500     | Tape and reel |
| STPS640CF     | STPS640CF | ISOWATT220AB | 2.08g  | 50       | Tube          |

■ Epoxy meets UL94,V0

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